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## NTE5332SM & NTE5334SM Silicon Bridge Rectifier, 1A

**Features:**

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Surge Current Capability
- Designed for Surface Mount Application
- Plastic Material - UL Recognition Flammability Classification 94V-O

**Maximum Ratings and Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified, Single Phase, half wave, 60Hz, resistive or inductive load. For Capacitive Load, Derate Current by 20%)

Peak Repetitive Reverse Voltage, $V_{RRM}$	
NTE5332SM .....	600V
NTE5334SM .....	1000V
Working Peak Reverse Voltage, $V_{RWM}$	
NTE5332SM .....	600V
NTE5334SM .....	1000V
DC Blocking Voltage, $V_R$	
NTE5332SM .....	600V
NTE5334SM .....	1000V
RMS Reverse Voltage, $V_{R(RMS)}$	
NTE5332SM .....	420V
NTE5334SM .....	700V
Average Rectified Output Current ( $T_A = +40^\circ\text{C}$ ), $I_O$	1A
Non-Repetitive Peak Forward Surge Current, $I_{FSM}$	
(8.3ms Single Half Sine-Wave Superimposed on Rated Load)	50A
Forward Voltage per Element ( $I_F = 1A$ )	1.1V
Peak Reverse Current at Rated DC Blocking Voltage(Note 1), $I_{RM}$	
$T_A = +25^\circ\text{C}$ .....	5 $\mu\text{A}$
$T_A = +125^\circ\text{C}$ .....	500 $\mu\text{A}$
Typical Junction Capacitance per Element (Note 1), $C_j$	25pF
Operating Junction Temperature Range, $T_j$	-65° to +150°C
Storage Temperature Range, $T_{STG}$	-65° to +150°C
Typical Thermal Resistance (Per Leg, Note 2),	
Junction-to-Ambient, $R_{thJA}$ .....	40°C/W
Junction-to-Case, $R_{thJL}$ .....	15°C/W

Note 1. Measured at 1.0MHz and applied reverse voltage of 4.0 Volts.

Note 2 Mounted on PC bard with 13mm<sup>2</sup> copper pad.

